

Pedro LÃ³pez

List of Publications by Year in descending order

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19
papers

166
citations

1307594

7
h-index

1125743

13
g-index

19
all docs

19
docs citations

19
times ranked

128
citing authors

#	ARTICLE	IF	CITATIONS
1	Atomistic analysis of the evolution of boron activation during annealing in crystalline and preamorphized silicon. <i>Journal of Applied Physics</i> , 2005, 97, 103520.	2.5	34
2	Physical insight into boron activation and redistribution during annealing after low-temperature solid phase epitaxial regrowth. <i>Applied Physics Letters</i> , 2006, 88, 191917.	3.3	22
3	Improved atomistic damage generation model for binary collision simulations. <i>Journal of Applied Physics</i> , 2009, 105, 083530.	2.5	22
4	Atomistic modeling of dopant implantation and annealing in Si: damage evolution, dopant diffusion and activation. <i>Computational Materials Science</i> , 2005, 33, 92-105.	3.0	21
5	Role of silicon interstitials in boron cluster dissolution. <i>Applied Physics Letters</i> , 2005, 86, 031908.	3.3	16
6	Atomistic analysis of the annealing behavior of amorphous regions in silicon. <i>Journal of Applied Physics</i> , 2007, 101, 093518.	2.5	14
7	Evolution of boron-interstitial clusters in preamorphized silicon without the contribution of end-of-range defects. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 154-155, 247-251.	3.5	7
8	Molecular dynamics simulation of the early stages of self-interstitial clustering in silicon. <i>Materials Science in Semiconductor Processing</i> , 2016, 42, 235-238.	4.0	7
9	Improved physical models for advanced silicon device processing. <i>Materials Science in Semiconductor Processing</i> , 2017, 62, 62-79.	4.0	5
10	The role of silicon interstitials in the deactivation and reactivation of high concentration boron profiles. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 114-115, 193-197.	3.5	4
11	On the anomalous generation of $\{0\hat{\alpha}\%0\hat{\alpha}\%1\}$ loops during laser annealing of ion-implanted silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2019, 458, 179-183.	1.4	4
12	Simulation of p-n junctions: Present and future challenges for technologies beyond 32 nm. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, C1A1-C1A6.	1.2	3
13	Degradation in Si Devices in Harsh Radiation Environments: Modeling of Damage-Dopant Interactions. , 2018, , .		2
14	Atomistic analysis of B clustering and mobility degradation in highly B-doped junctions. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2010, 23, 266-284.	1.9	1
15	Carrier mobility degradation in highly B-doped junctions. , 2009, , .		1
16	Simulation study of ion implanted defects associated to luminescence centers in silicon. , 2011, , .		1
17	Identification of Extended Defect Atomic Configurations in Silicon Through Transmission Electron Microscopy Image Simulation. <i>Journal of Electronic Materials</i> , 2018, 47, 4955-4958.	2.2	1
18	Extending defect models for Si processing: The role of energy barriers for defect transformation, entropy and coalescence mechanism. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2022, 512, 54-59.	1.4	1

#	ARTICLE	IF	CITATIONS
19	Atomistic modeling of laser-related phenomena. , 2021, , 79-136.		0